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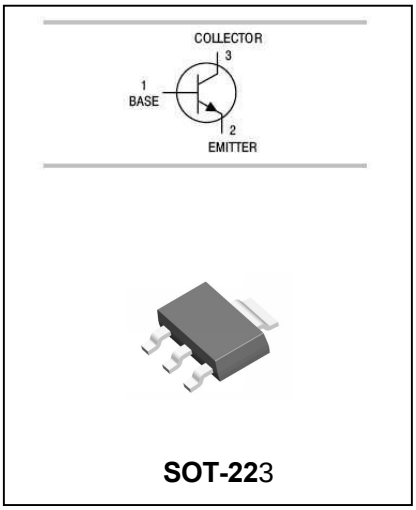
NPN Epitaxial Planar Silicon Transistors FZT651TA

FEATURES

- Fast switching speed.
- Low collector-to-emitter saturation voltage.
- Large current capacity and wide ASO.

Lead-free

HF



SOT-223

ORDERING INFORMATION

Type No.	Marking	Package Code
FZT651TA	FZT651	SOT-223

□: none is for Lead Free package;
"G" is for Halogen Free package.

MAXIMUM RATING @ Ta=25℃ unless otherwise specified

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	50	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current –DC -Pulse	3 6	A
P_C	Collector Dissipation	0.5 1.5(Note1)	W
T_j,T_{stg}	Junction and Storage Temperature	-55 to+150	℃

Note
1. Mounted on ceramic board (250mm^2×0.8mm)

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ELECTRICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=10μA I_E=0	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=1mA I_B=0	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=10μA I_C=0	6			V
Collector cut-off current	I_{CBO}	V_{CB}=40V I_E=0			1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=4V,I_C=0			1	μA
DC current gain	H_{FE}	V_{CE}=2V I_C=100mA V_{CE}=2V I_C=3A	100 35		560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=2A I_B=100mA		0.35	0.7	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=2A I_B=100mA		0.94	1.2	V
Transition frequency	f_T	V_{CE}=10V,I_C=50mA,		150		MHz
Output Capacitance	C_{ob}	V_{CB}=10V f=1.0MHz I_E=0		39		pF

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TYPICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified

